

Silicon PNP Power Transistors

2SA636 2SA636A

DESCRIPTION

- With TO-202 package
- Complement to type 2SC1098/1098A
- High breakdown voltage
- High transition frequency

APPLICATIONS

- For audio frequency power amplifier and low speed switching applications

PINNING(see Fig.2)

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |

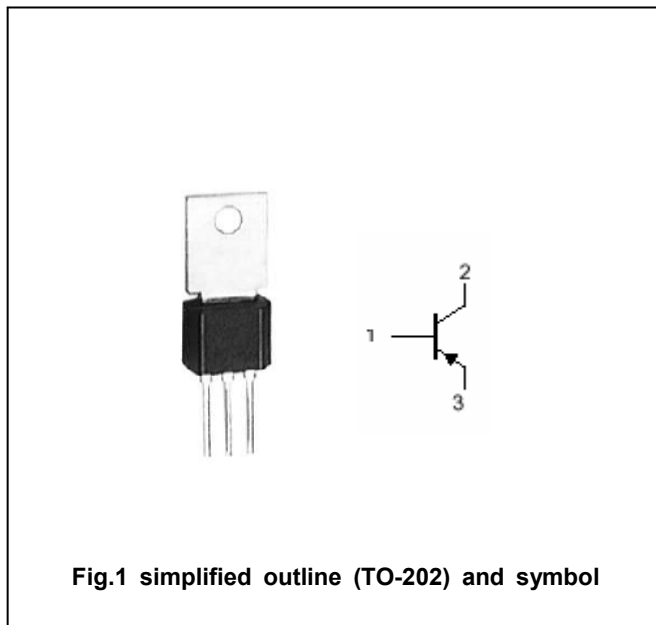


Fig.1 simplified outline (TO-202) and symbol

Absolute maximum ratings (Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|---------------------------|----------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | -70 | V |
| V _{CEO} | Collector-emitter voltage | 2SA636 | -45 | V |
| | | 2SA636A | -60 | |
| V _{EBO} | Emitter-base voltage | Open collector | -5 | V |
| I _C | Collector current | | -3 | A |
| I _{CM} | Collector current-peak | | -5 | A |
| I _B | Base current | | -0.6 | A |
| P _T | Total power dissipation | T _C =25°C | 10 | W |
| | | T _a =25°C | 1.2 | |
| T _j | Junction temperature | | 150 | °C |
| T _{stg} | Storage temperature | | -55~150 | °C |

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CHARACTERISTICS

T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|--------------------|--------------------------------------|--|-----|------|------|------|
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-1.5A ; I _B =-0.15A | | -0.5 | -2.0 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =-1.5A ; I _B =-0.15A | | -0.8 | -2.0 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =-45V; I _E =0 | | | -1 | μA |
| I _{EBO} | Emitter cut-off current | V _{EB} =-3V; I _C =0 | | | -1 | μA |
| h _{FE-1} | DC current gain | I _C =-20mA ; V _{CE} =-5V | 20 | | | |
| h _{FE-2} | DC current gain | I _C =-0.5A ; V _{CE} =-5V | 40 | | 250 | |
| C _{OB} | Output capacitance | I _E =0; V _{CB} =-10V; f=1MHz | | 60 | | pF |
| f _T | Transition frequency | I _C =-0.1A ; V _{CB} =-5V | | 45 | | MHz |

◆ h_{FE-2} classifications

| N | M | L | K |
|-------|--------|--------|---------|
| 40-60 | 50-100 | 80-160 | 120-250 |

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PACKAGE OUTLINE

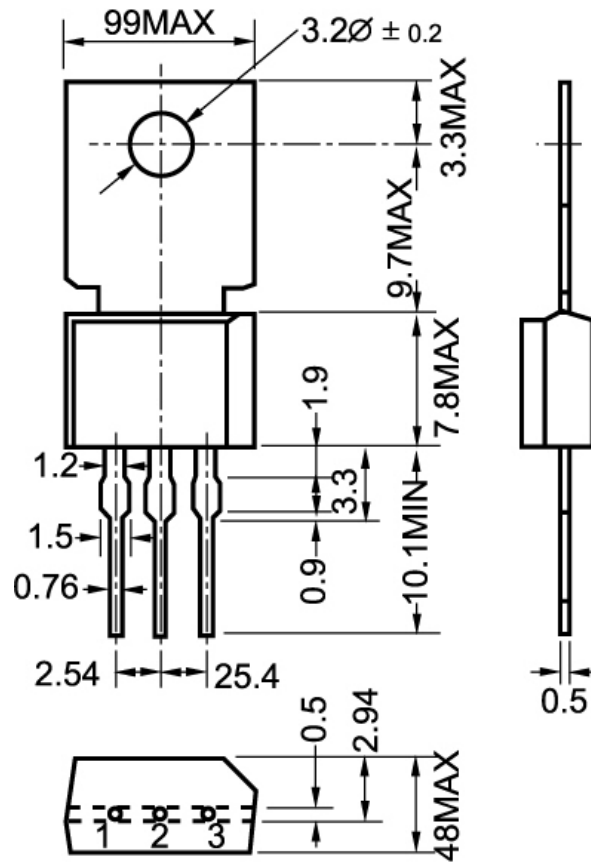


Fig.2 outline dimensions